

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-36. (Canceled)

37. (Currently Amended) An atmosphere for a chemical vapor deposition process, comprising:
a deposition gas having a chemical reactivity with a reactant gas; and
a chemically inert ~~reactability increaser~~ reaction promoter mixed with said deposition gas
at a rate of about 0.4 to 0.6 of a rate of flow of the reactant gas to form a high density plasma at a
total pressure of greater than 1 millitorr.

38. (Currently Amended) The atmosphere of claim 37 wherein said deposition gas is a film
precursor deposition gas having a flow rate of greater than 10 sccm.

39. (Currently Amended) The atmosphere of claim 37 wherein said deposition gas is a metal
film precursor deposition gas, the reactant gas includes hydrogen at a flow rate of about 10,000
sccm, and the reaction promoter includes argon at a flow rate of at least 4,000 sccm.

Claims 40-66. (Canceled)